# International

PD-2.380 Provisional Data Sheet HFA45HI60C

# HEXFRED<sup>™</sup> ULTRA FAST, SOFT RECOVERY DIODE 600V, 45A

#### **Major Ratings and Characteristics**

Characteristics		Units
V <sub>br</sub> (per leg)	600	V
IF(AV)	45*	A
t <sub>rr</sub> (per leg)	75	ns
Q <sub>rr</sub> (per leg)	375	nC
IRRM (per leg)	10	A
VF (per leg)	1.7	v

\*IF limited by pin diameter

## Description

International Rectifier's HFA45HI60C is a state of the art ultra fast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available.

With basic ratings of 600 volts and 45 amps continuous current, the HFA45HI6OC is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultra fast recovery time, the HEXFRED product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the b portion of recovery.

## Features:

- Ultrafast Recovery
- Ultra Soft Recovery
- Very Low IRRM - Very Low Qrr
- Guaranteed Avalanche
- Specified at Operating Conditions
- Hermetic
- Electrically Isolated
- Ceramic Évelets

#### Benefits:

- Reduced RFI and EMI
- Reduced Power Loss in Diode and Switching Transistor
- Higher Frequency Operation
- Reduced Snubbing
- Reduced Parts Count

The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes.

The HEXFRED HFA45HI60C is ideally suited for applications in power supplies and power conversion systems (such as inverters, converters, UPS systems, and power factor correction circuits), motor drives, and many other similar applications where high speed, high efficiency rectification is needed.



# Voltage Ratings: TJ = 25 - 150°C

Parameter			Units	
V <sub>br</sub> (per leg)	Max D.C. Reverse Voltage (V)	600	v	
Viso (per leg)	Max PK Repetitive Reverse Voltage (V)	l		70К ft, I <sub>R</sub> < 25µА

# Absolute Maximum Ratings

Parameter		Min	Тур	Max	Units	Conditions
F(AV)	Max Average Forward Current	-	-	45*		$T_C = 100^{\circ}C$ , d.c. = 50%, rect. wave $V_R = 0.8 V_{RRM}$
IFSM (per leg)	Max Single Pulse Forward Current	-	-	225	<b>A</b>	T <sub>C</sub> = 25°C, 1/2 Sine Wave, 60 Hz P.W. = 8.33 ms
AS	Max Single Pulse Avalanche Current	-		2	1	L = 100 µH, I <sub>F</sub> = 45A

\*Ir limited by pin diameter

# Electrical Specifications: TJ = 25°C unless otherwise specified

Parameter		Min	Тур	Max	Units	Conditions
VFM (per leg)	M (per leg) Max Forward Voltage	-	-	1.7	v	1F = 22A
		-	-	2.0		1F = 45A
		-	—	1.5		IF = 22A, Tj = 125°C
IRM (per leg)	Max Reverse Leakage Current	-	_	10	μA	VR = VR Rated
		-	-	1.0	mA	TJ = 125°C, VR = 0.8 x VR Rated
C <sub>T</sub> (per leg)	Junction Capacitance	-	-	100	pF	VR = 200V
Ls	Internal Source Inductance	-	13	-	nH	Measured lead to lead 5mm from package body

# Dynamic Recovery Specifications: TJ = 25°C unless otherwise specified

Parameter		Min	Тур	Max	Units	Conditions
t <sub>rr</sub> (per leg)	Reverse Recovery Time	-	-	75	ns	$I_F = 22A$ , di/dt $\leq 200A/\mu s$ , $V_R = 200V$
IRRM (per leg)	Max Reverse Recovery Current		-	10	A	$i_{\rm F} = 22$ A, di/dt $\leq 200$ A/ $\mu$ s, V <sub>R</sub> = 200V
Q <sub>RR</sub> (per leg)	Reverse Recovered Charge	-	-	375	nC	$I_F = 22A$ , di/dt $\leq 200A/\mu s$ , $V_P = 200V$

# **Thermal-Mechanical Specifications**

Parameter		Min	Тур	Max	Units	Conditions
TJ, TSTG	Junction and Storage Temp Range	-55	-	150	°C	
RAJC	Thermal Resistance; Junction to Case	-	-	1.20	K/W	
WT	Weight	-	10.9	-	g	
Case	TO-259AA		JE	DEC		